

AMENDMENTS TO THE CLAIMS:

1. (Previously Presented) A photomask comprising:
 - a mask pattern formed on a transparent substrate and having a light shielding property with respect to exposing light; and
 - a transparent portion of said transparent substrate where said mask pattern is not formed, wherein said transparent portion surrounds said mask pattern,
 - said mask pattern includes a first pattern and a second pattern each having a line shape and having a mask enhancer structure including a phase shifter for transmitting said exposing light in an opposite phase with respect to said transparent portion and a shielding portion surrounding said phase shifter, and a third pattern located adjacent to said first pattern along a direction vertical to the line direction of said first pattern, at a distance not larger than a given distance and with a transparent portion sandwiched between said first pattern and said third pattern,
 - an end portion of said first mask pattern and an end portion of said second mask pattern are surrounded by said transparent portion in three directions of the end portion of the first mask pattern and the end portion of the second mask pattern,
 - the outermost region in said mask pattern is said shielding portion, and the outmost region of said third pattern is a shielding pattern,
 - a first phase shifter in said first pattern is a line-shaped pattern having a first line width with a predetermined width,
 - a second phase shifter in said second pattern is a line-shaped pattern having a second line width with a predetermined width,
 - said first line width is smaller than said second line width, and

a pattern width of said first pattern in a short side direction is the same as a pattern width of said second pattern in a short side direction.

2. (Original) The photomask of Claim 1, wherein each of regions of said transparent portion disposed on both sides of said second pattern has a width larger than a given dimension.

3. (Original) The photomask of Claim 2, wherein said third pattern has the mask enhancer structure or is made of a shielding portion.

4. (Original) The photomask of Claim 3, wherein said third pattern is provided with a semi-shielding portion for partially transmitting the exposing light in an identical phase with respect to said transparent portion instead of said shielding portion of the mask enhancer structure.

5. (Previously presented) The photomask of Claim 1,
wherein said mask pattern further comprises a fourth pattern,
said fourth pattern is located adjacent to said second pattern at a distance not larger than said given distance with said transparent portion sandwiched between said fourth pattern and said second pattern along a direction vertical to the line direction of said second pattern, and
the distance between said second pattern and said fourth pattern is larger than the distance between said first pattern and said third pattern.

6. (Original) The photomask of Claim 5, wherein each of said third pattern and said fourth pattern has the mask enhancer structure or is made of a shielding portion.

7. (Original) The photomask of Claim 6, wherein each of said third pattern and said fourth pattern is provided with a semi-shielding portion for partially transmitting the exposing

light in an identical phase with respect to said transparent portion instead of said shielding portion of the mask enhancer structure.

8-9. (Cancelled)

10. (Original) The photomask of Claim 1, wherein said first pattern and said second pattern are connected to each other, thereby forming one continuous pattern.

11. (Original) The photomask of Claim 1, wherein said given distance is not larger than $(\lambda/NA) \times M$, wherein λ indicates a wavelength of the exposing light and M and NA respectively indicate a reduction ratio and numerical aperture of a reduction projection optical system of a projection aligner.

12. (Previously Presented) The photomask of Claim 1, wherein each of said first pattern and said second pattern has a pattern width not larger than $(0.8 \times \lambda/NA) \times M$, wherein λ indicates a wavelength of the exposing light and M and NA respectively indicate a reduction ratio and numerical aperture of a reduction projection optical system of a projection aligner.

13-14. (Cancelled)

15. (Original) The photomask of Claim 1, wherein each of said first pattern and said second pattern is provided with a semi-shielding portion for partially transmitting the exposing light in an identical phase with respect to said transparent portion instead of said shielding portion of the mask enhancer structure.

16. (Original) The photomask of Claim 15, wherein said semi-shielding portion transmits the exposing light with a phase difference not less than $(-30 + 360 \times n)$ degrees and not

more than $(30 + 360 \times n)$ degrees (wherein n is an integer) with respect to said transparent portion.

17. (Original) The photomask of Claim 15, wherein said semi-shielding portion is made of a metal thin film with a thickness of 30 nm or less.

18. (Previously Presented) The photomask of Claim 1, wherein said first phase shifter and said second phase shifter transmit the exposing light with a phase difference not less than $(150 + 360 \times n)$ degrees and not more than $(210 + 360 \times n)$ degrees (wherein n is an integer) with respect to said transparent portion.

19. (Previously Presented) The photomask of Claim 1, wherein said first phase shifter and said second phase shifter are formed by trenching said transparent substrate.

20-29. (Cancelled)

30. (Previously presented) The photomask of Claim 1, wherein said third pattern is another pattern separated from said first and second patterns.

31. (Previously presented) The photomask of Claim 1, wherein each of said first and second patterns has a length of $2 \times \lambda \times M$ or more, wherein λ indicates a wavelength of the exposing light and M indicates a reduction ratio of a reduction projection optical system of a projection aligner.

32. (New) A pattern formation method using the photomask of Claim 1, comprising the steps of:

forming a resist film on a substrate;

irradiating said resist film with the exposing light through said photomask; and
forming a resist pattern by developing said resist film having been irradiated with the
exposing light.

33. (New) The pattern formation method of Claim 32,
wherein oblique incident illumination is employed in the step of irradiating said resist
film with the exposing light.